

L Number	Hits	Search Text	DB	Time stamp
1	504784	((semiconductor si silicon gaas p n) with (substrate))	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:05
2	41054	((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate)))	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:05
3	573358	high with (current power)	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:05
4	104885	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:07
5	10060	((semiconductor si silicon gaas p n) with (substrate)) same interconnect	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:07
6	1197	((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power))	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:08
7	8366	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes) and ((multiple different plurality) with (metal interconnect))	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:10
8	78	((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power)) and ((multiple different plurality) with (metal interconnect))	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:17
9	4691	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes) and ((multiple different plurality) with (metal interconnect))) and (diffusion barrier)	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:19
10	4691	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes) and ((multiple different plurality) with (metal interconnect))) and (diffusion barrier)	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/09/17 14:19

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2	41054	((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate)))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:05
3	573358	high with (current power)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:06
4	104885	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:07
5	10060	((semiconductor si silicon gaas p n) with (substrate)) same interconnect	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:07
6	1197	((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:08
7	8366	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)) and ((multiple different plurality) with (metal interconnect))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:10
8	78	((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power)) and ((multiple different plurality) with (metal interconnect))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:10
9	4691	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)) and ((multiple different plurality) with (metal interconnect))) and (diffusion barrier)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:19
10	4691	((semiconductor si silicon gaas p n) with (substrate)) same (opening via grooves slots holes)) and ((multiple different plurality) with (metal interconnect))) and (diffusion barrier)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:19
11	262	((semiconductor si silicon gaas p n) with (substrate)) same ((epitaxial epi) same ((semiconductor si silicon gaas p n) with (substrate))) same (high with (current power))) and (different with (metal layer interconnect))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/09/17 14:21